

Amendments to the Specification

Please add the following new section at page 1, between lines 3 and 4, of the specification:

CROSS-REFERENCE TO RELATED APPLICATIONS

A claim of priority is made to U.S. provisional patent application no. 60/457,323, filed March 26, 2003, and to British patent application no. 0305544.9, filed March 11, 2003.

Please rewrite the paragraphs appearing at page 3, lines 26-29, to read as follows:

Figure 6 is a corresponding graph for resistivity against power, with no bias voltage; and

Figure 7 compares film characteristics for a tungsten nitride film deposited using argon and krypton respectively;

Figure 8 compares voltage, current and pressure conditions using argon and krypton; and

Figure 9 shows the effect of changing the sputter gas on the stress of a tungsten film.